

## INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

## STP25N10F7

### FEATURES

- Drain Current –I\_D= 25A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-
- : V<sub>DSS</sub>= 100V(Min)
- Static Drain-Source On-Resistance
- : R<sub>DS(on)</sub> = 0.035 Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

- These devices utilize the 7th generation of design rules of ST Proprietary, with a new gate structure.
- Low Drain-Source On-Resistance

### APPLICATIONS

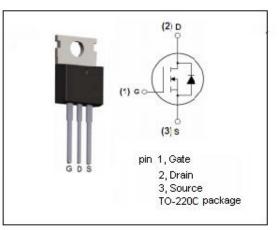
Switching application

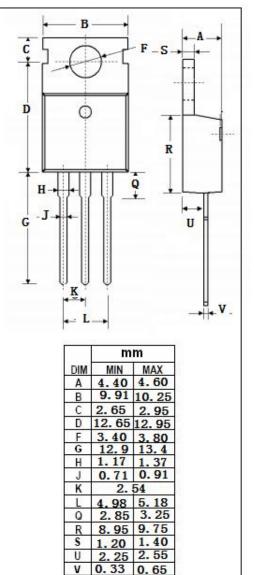
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT		
V <sub>DSS</sub>	Drain-Source Voltage	100	V		
V <sub>GS</sub>	Gate-Source Voltage-Continuous	±20	V		
ID	Drain Current-Continuous	25	A		
IDM	Drain Current-Single Pluse	100	А		
PD	Total Dissipation @T <sub>C</sub> =25℃	50	W		
TJ	Max. Operating Junction Temperature	175	°C		
T <sub>stg</sub>	Storage Temperature	-55~175	°C		

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	3	°C/W
R <sub>th j-a</sub>	Thermal Resistance, Junction to Ambient	62.5	°C/W





isc website: <u>www.iscsemi.com</u>



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### **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA	100		V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> = 0.25mA		4.5	V
$R_{\text{DS}(\text{on})}$	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 12.5A		0.035	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0		±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0 V <sub>DS</sub> = 100V; V <sub>GS</sub> = 0; T <sub>j</sub> = 125℃		10 100	μA
$V_{\text{SD}}$	Forward On-Voltage	I <sub>S</sub> = 25A; V <sub>GS</sub> =0		1.1	V

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